





#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	Package	I <sub>D MAX</sub> T <sub>C</sub> = +25°C	
650V	$1.3\Omega$ @ $V_{GS} = 10V$	ITO220AB	9.0A	

## **Description**

This new generation complementary dual MOSFET features low onresistance and fast switching, making it ideal for high-efficiency power management applications.

## **Applications**

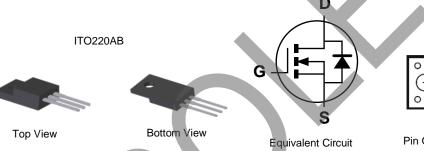
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

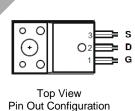
## **Features**

- Low Input Capacitance
- High BV<sub>DSS</sub> Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: ITO220AB
- Case Material: Molded Plastic, "Green" Molding Compound;
  UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)





### Ordering Information (Note 4)

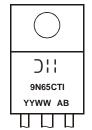
Part Number	Case	Packaging
DMG9N65CTI	ITO220AB	50 pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

ITO220AB



○ I = Manufacturer's Marking
 9N65CTI = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 19 = 2019)
 WW = Week (01 to 53)

DMG9N65CTI Document number: DS36027 Rev. 5 - 4



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic				Value	Unit
Drain-Source Voltage				650	V
Gate-Source Voltage				±30	V
Continuous Drain Current (Notes 5 & 6)	Steady	$T_C = +25$ °C		9.0	_
V <sub>GS</sub> = 10V	State	$T_C = +70$ °C	ID	7.0	A
Pulsed Drain Current (Note 7) 10µs Pulse, Pulse Duty Cycle<=1%				30	A
Avalanche Current (Note 8) V <sub>DD</sub> = 100V, V <sub>GS</sub> = 10V, L = 60mH			$I_{AR}$	2.7	A
Repetitive Avalanche Energy (Note 8) V <sub>DD</sub> = 100V, V <sub>GS</sub> = 10V, L = 60mH				260	mJ

## **Thermal Characteristics**

Characteristic				Max		Unit
Dower Dissination (Note 5)	$T_C = +25$ °C	)	13		W	
Power Dissipation (Note 5)	$T_C = +70$ °C	P <sub>D</sub>		8	8	
Thermal Resistance, Junction to Case (Note 5)	$T_C = +25^{\circ}C$	R <sub>0</sub> JC		8.84		°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150			°C

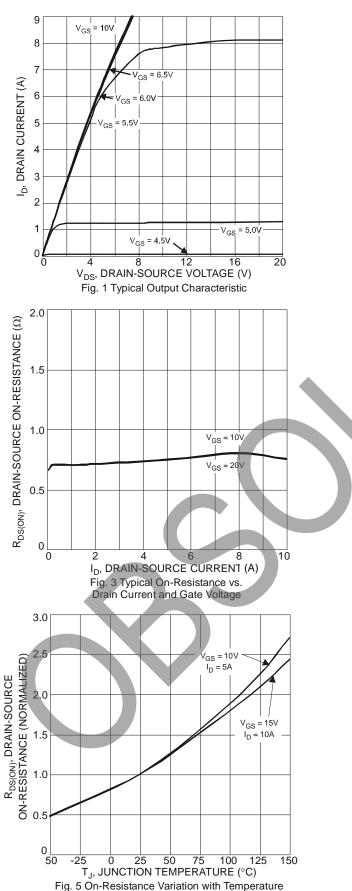
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

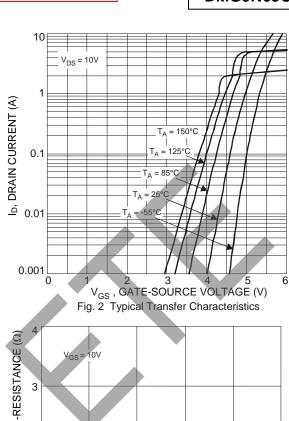
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	650	$\sim$	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_		1.0	μΑ	$V_{DS} = 650V, V_{GS} = 0V$	
Gate-Source Leakage	$I_{GSS}$		_	±100	nA	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	3	_	5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		0.7	1.3	Ω	$V_{GS} = 10V, I_D = 4.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	I	8.5	_	S	$V_{DS} = 40V, I_{D} = 4.5A$	
Diode Forward Voltage	$V_{SD}$	1	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	2310	_		.,	
Output Capacitance	Coss	_	122	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.2	_	T = 1.0MHZ		
Gate Resistance	$R_g$	1	2.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	39	_		101/1/ 5001/	
Gate-Source Charge	$Q_{gs}$	1	8.5	_	nC	$V_{GS} = 10V, V_{DS} = 520V,$ $I_{D} = 8A$	
Gate-Drain Charge	$Q_{gd}$	l	11.9	_		ID = OA	
Turn-On Delay Time	t <sub>D(on)</sub>	_	39	_	ns		
Turn-On Rise Time	t <sub>r</sub>	1	29	_	ns	$V_{GS} = 10V, V_{DS} = 325V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	122	_	ns	$R_g = 25\Omega$ , $I_D = 8A$	
Turn-Off Fall Time	t <sub>f</sub>	-	28	_	ns		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	570	_	ns	$dI/dt = 100A/\mu s$ , $V_{DS} = 100V$ ,	
Body Diode Reverse Recovery Charge	Qrr	_	4.17	_	μC	$I_F = 8A$	

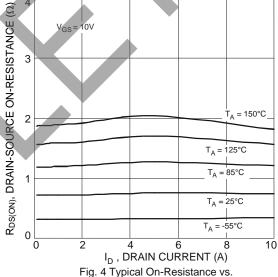
Notes:

- 5. Device mounted on an infinite heatsink.
- 6. Drain current limited by maximum junction temperature.
- 7. Repetitive rating, pulse width limited by junction temperature.
- 8.  $I_{AR}$  and  $E_{AR}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to production testing.

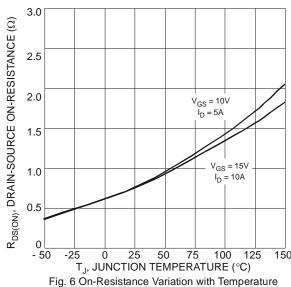








Drain Current and Temperature





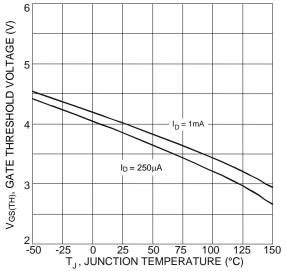
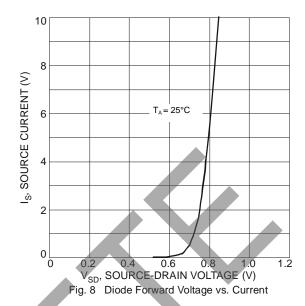


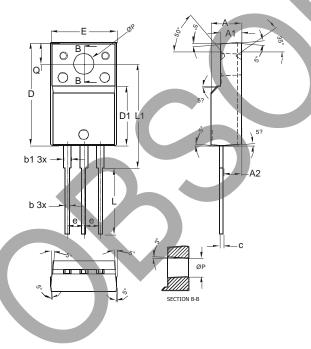
Fig. 7 Gate Threshold Variation vs. Junction Temperature



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### ITO220AB



ITO220AB						
Dim	Min	Тур	Max			
Α	4.50	4.70	4.90			
A1	3.04	3.24	3.44			
A2	2.56	2.76	2.96			
b	0.50	0.60	0.75			
b1	1.10	1.20	1.35			
С	0.50	0.60	0.70			
D	15.67	15.87	16.07			
D1	8.99	9.19	9.39			
е		2.54				
Е	9.91	10.11	10.31			
L	9.45	9.75	10.05			
L1	15.80	16.00	16.20			
Р	2.98	3.18	3.38			
Q	3.10	3.30	3.50			
All Dimensions in mm						



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